

FILE EAST: [10348910.gate around channel.wsp:1]

File View Edit Tools Window Help

L10: (41) "Adkisson James".in.

L11: (5) "ep 202335"

L12: (0) 08/681353

L13: (572114) nm nanometer nano adj meter angstrom ang

L14: (1) 4 and 13

L15: (32) 4 9

L16: (27) 15 and 13

L17: (133813) finfet fin

L18: (0) 18 and 17

L19: (294) (finfet fin adj2 (fet mosfet mos transistor))

L20: (3080) double adj gate

L21: (850784) buried adj oxide box

L22: (15) 20 with 21

L23: (60) 20 same 21

L25: (21) 19 and 23

L24: (333) 19 23

L26: (29748299) (@ad @pd) < 20030123

L27: (256) 24 and 28

L28: (2866582) thickness width

L28: (126596) 13 near4 28

L30: (179) 27 and 28

L31: (66) 29 near8 17

L32: (19) 31 and 27

L33: (2) "20020140039"

Failed

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Default operator: OR

Plurals

Highlight all hit terms equally

31 and 27

Nov 2004

ALL NEW ALL NEW Image Refs

	U	I	Investor	Document	Issue	P	Title	Current	Current	XR	Re	Retrieval	S	C	P	I	Image	Doc	P
1			Lee, Jong Ho	US 6768158	20040	1	Flash memory element and manufacturing me	257/315	257/317								US 676815		
2			Fried, David	US 6750487	20040	1	Dual double gate transistor	257/270	257/206								US 675048		
3			Yeo, Yee-Chia	US 2004011	20040	1	CMOS inverters configured using multiple-ga	438/198									US 200401		
4			Chen, Hao-Yu	US 2004010	20040	1	Multiple-gate transistor structure and metho	257/202									US 200401		
5			Krivokapic, Z	US 2004010	20040	1	Two transistor nor device	326/112	257/E27.06								US 200401		
6			Yeo, Yee-Chia	US 2004009	20040	1	Strained-channel multiple-gate transistor	257/317									US 200400		
7			Fried, David	US 2003019	20031	1	FIN MEMORY CELL AND METHOD OF FABRI	257/200									US 200301		
8			Fried, David	US 2003019	20031	1	Dual double gate transistor and method for f	257/328	257/331								US 200301		
9			Fischetti, Ma	US 2003019	20031	1	Germanium field effect transistor and metho	439/305	257/E21.63								US 200301		
10			Fried, David	US 2003014	20030	1	Fin-type resistors	257/536	257/378								US 200301		

100 Details RS-RTM

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ALUM